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High-efficiency normal-incidence vertical p-i-n photodetectors on a germanium-on-insulator platform: publisher’s note

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This publisher’s note reports corrections to Eq. (1) in [Photon. Res. 5, 702 (2017)]. © 2017 Chinese Laser Press

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Equation (1) was corrected in the article [1] from

\[ I_{\text{dark}} = BT^{1.5} e^{\frac{qV}{kT}} \{ \exp\left[ qV/(e2kT) \right] - 1 \} \]

to

\[ I_{\text{dark}} = BT^{1.5} e^{\frac{qV}{kT}} \left( e^{\frac{qV}{kT}} - 1 \right) \]

The article [1] was corrected online as of 27 November 2017.

REFERENCE